

### The Memory Hierarchy

15-213/18-213/15-513/18-613: Introduction to Computer Systems 10<sup>th</sup> Lecture, March 9<sup>th</sup>, 2021

#### **Announcements**

- Midterm Exam Logistics (Tentative)
  - Available Tuesday the 16<sup>th</sup> Thursday the 18<sup>th</sup>
  - 3 hours, download through upload
    - The exam is what we'd typically give in 80 minutes, but we are allowing extra time to handle technical issues and because, in this mode, we aren't rushed by class changes.
    - Extra time, etc, provided according to accommodations
  - Via Gradescope
  - Permitted resources:
    - Materials the course staff has supplied to you, e.g. via the official course Web page, Canvas, or Autolab, including directly linked materials, and the suggested/required textbooks. Additionally, those books suggested by course staff on Piazza are allowed.
  - Self-proctored
  - Taking a break is okay, but it counts toward the 3 hour time limit and you must avoid exposure to all but allowed resources during the break.

### Exam Scope 1/4

- Bits, Bytes, and Ints: Student should be able to convert among 2s complement, regular binary, hexadecimal, and decimal representations; do arithmetic; recognize and manage overflow and underflow and the numerical consequences; be able to recognize and write out important bit patterns; articulate limits; as well as be able to use C's casting rules and do datalab-style problems.
- Floats: Student should be able to recognize and translate numbers from into and out of IEEE-style representations, both normalized and denormalized; do arithmetic upon IEEE-style numbers, including that which crosses over the norm/denorm boundary and results in special numbers, e.g. NaN, infinity; recognize and articulate special bit patterns; round numbers; cast and compare among float and non-float types using C's rules; and do datalab style puzzles.

### Exam Scope 2/4

- Machine programming: Students should be able to read and write basic assembly, similar to the in class example, including that which requires if statements, and loops (for, while, do). Students should be careful to understand the behavior of mov operations from smaller into larger registers, e.g. %edx to %rax, set operations and movzbl and similar, and lea vs mov. Students should also be familiar with the condition flags, how and when they are set, and how they are used.
- Stack and calling convention: Students should understand the calling convention, including how registers are used to pass arguments, how caller- and callee- saved registers are managed across function calls, and how the stack is layed, for example, w.r.t. How, where, and in which stack frame (caller vs callee) allocations occur and what it looks like in assembly, e.g. local variables, arguments, and return address.

### Exam Scope 3/4

Data representation: Students should understand how arrays (dynamic and static) are represented in memory, how they are accessed in C and assembly, and what row-major ordering is and that it is used. They should understand how structs are organized in memory and how they are accessed in C and assembly. They should understand alignment, the alignment rules, and how this affects data, especially structs. They should understand to use sizeof() in C and why. They should be able to read and write code, in assembly and C, to access complex types, e.g. arrays of structs or structs containing arrays, or even arrays containing structs containing arrays. Students should be cautions about type sizes, e.g. statically allocated arrays vs pointers vs scalar types.

### Exam Scope 4/4

Caching: Students should understand the organization of direct and set-associative caches and be able to draw a figure representing the cache organization from the parameters. Given all but one of the parameters for a cache, students should be able to derive the missing parameter. Given a cache configuration and a set of memory accesses, students should be able to simulate the accesses to identify the hits, misses, and associated rates. Given C or assembly code which accesses memory within one or more loops, possibly nested, students should be able to estimate the hit or miss rate. Students should understand why the miss rate is a more intuitive metric than the hit rate. Given cache performance parameters, e.g. miss rates, and access times, students should be able to compute the effective memory access time.

### **Today**

- The memory abstraction
- RAM: main memory building block
- Locality of reference
- The memory hierarchy
- Storage technologies and trends

### **Writing & Reading Memory**

#### **■** Write

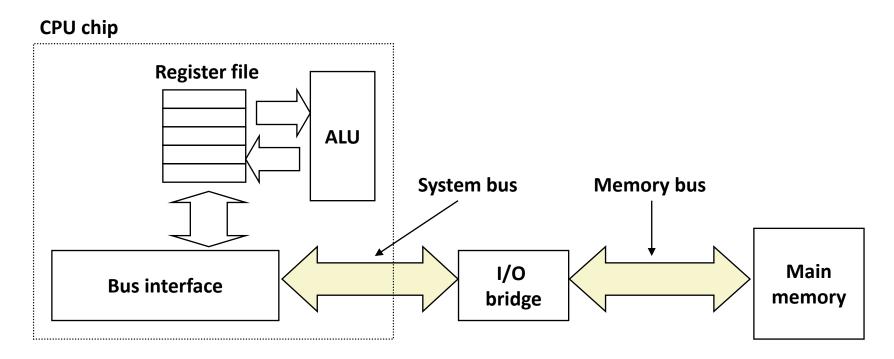
- Transfer data from CPU to memory movq %rax, 8(%rsp)
- "Store" operation

#### Read

- Transfer data from memory to CPU movq 8 (%rsp), %rax
- "Load" operation

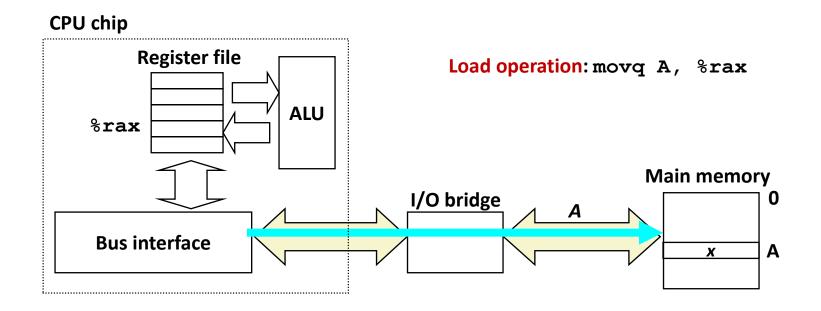
# **Traditional Bus Structure Connecting CPU and Memory**

- A bus is a collection of parallel wires that carry address, data, and control signals.
- Buses are typically shared by multiple devices.



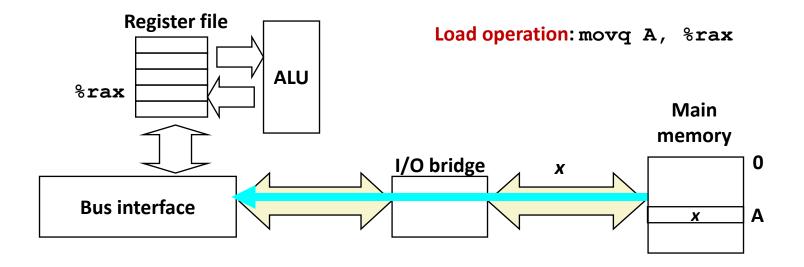
### **Memory Read Transaction (1)**

CPU places address A on the memory bus.



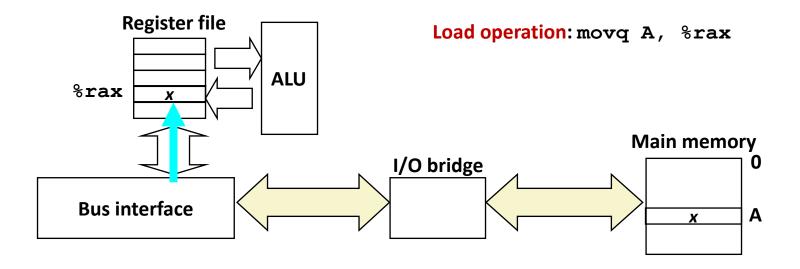
### **Memory Read Transaction (2)**

Main memory reads A from the memory bus, retrieves word x, and places it on the bus.



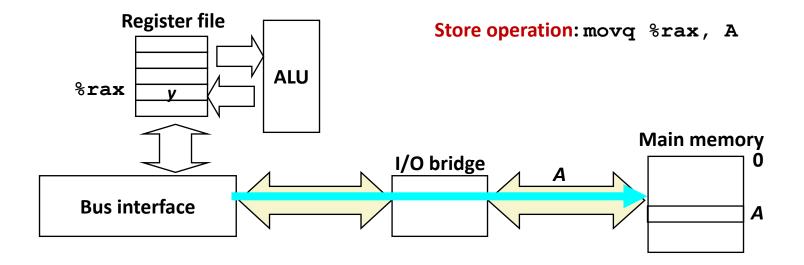
### **Memory Read Transaction (3)**

■ CPU read word x from the bus and copies it into register %rax.



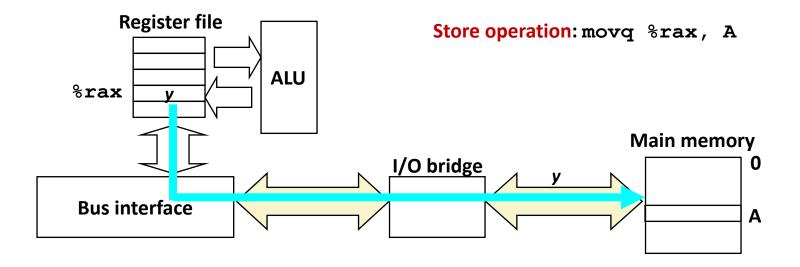
### **Memory Write Transaction (1)**

CPU places address A on bus. Main memory reads it and waits for the corresponding data word to arrive.



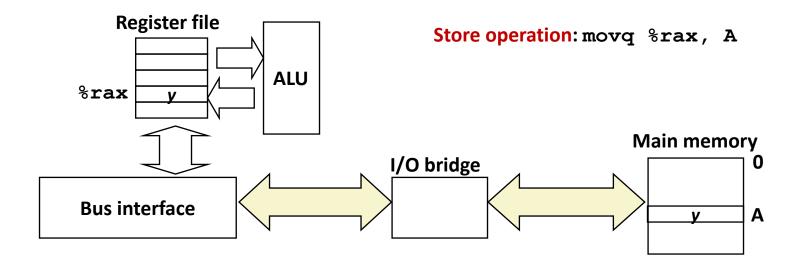
### **Memory Write Transaction (2)**

CPU places data word y on the bus.



### **Memory Write Transaction (3)**

Main memory reads data word y from the bus and stores it at address A.



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### Random-Access Memory (RAM)

#### Key features

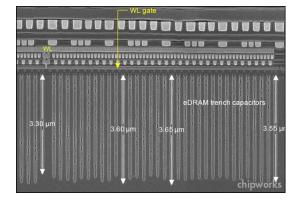
- RAM is traditionally packaged as a chip.
  - or embedded as part of processor chip
- Basic storage unit is normally a cell (one bit per cell).
- Multiple RAM chips form a memory.

#### RAM comes in two varieties:

- SRAM (Static RAM)
- DRAM (Dynamic RAM)

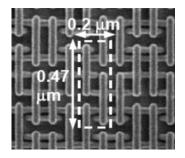
### **RAM Technologies**

DRAM



- 1 Transistor + 1 capacitor / bit
  - Capacitor oriented vertically
- Must refresh state periodically

SRAM



- 6 transistors / bit
- Holds state indefinitely (but will still lose data on power loss)

### **SRAM vs DRAM Summary**

	Trans. per bit	Access time	Needs refresh?	Needs PEDC?	Cost	Applications
SRAM	6 or 8	1x	No	Maybe	100x	Cache memories
DRAM	1	10x	Yes	Yes	1x	Main memories, frame buffers

EDC: Error detection and correction

#### Trends

- SRAM scales with semiconductor technology
  - Reaching its limits
- DRAM scaling limited by need for minimum capacitance
  - Aspect ratio limits how deep can make capacitor
  - Also reaching its limits

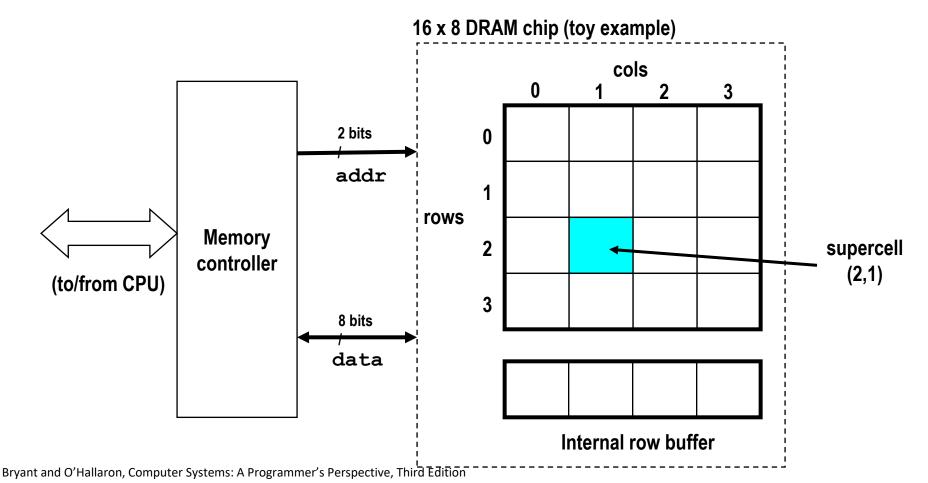
### **Enhanced DRAMs**

- Operation of DRAM cell has not changed since its invention
  - Commercialized by Intel in 1970.
- DRAM cores with better interface logic and faster I/O :
  - Synchronous DRAM (SDRAM)
    - Uses a conventional clock signal instead of asynchronous control
  - Double data-rate synchronous DRAM (DDR SDRAM)
    - Double edge clocking sends two bits per cycle per pin
    - Different types distinguished by size of small prefetch buffer:
      - DDR (2 bits), DDR2 (4 bits), DDR3 (8 bits), DDR4 (16 bits)
    - By 2010, standard for most server and desktop systems
    - Intel Core i7 supports DDR3 and DDR4 SDRAM

### **Conventional DRAM Organization**

#### $\blacksquare$ $d \times w DRAM$ :

•  $d \cdot w$  total bits organized as d supercells of size w bits

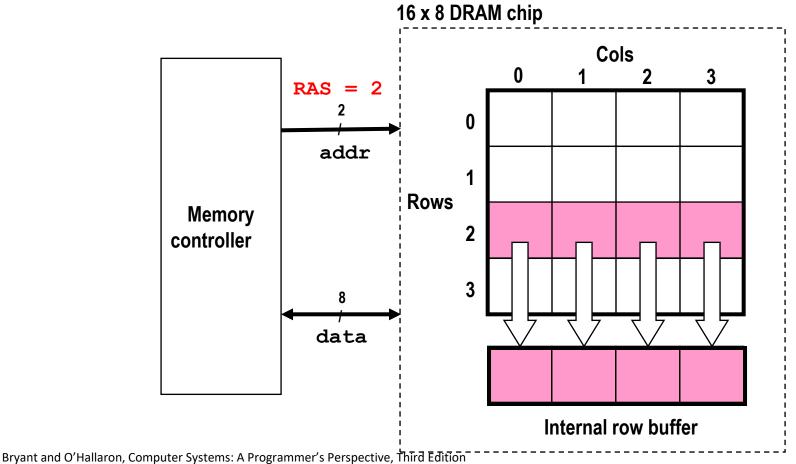


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### Reading DRAM Supercell (2,1)

Step 1(a): Row access strobe (RAS) selects row 2.

**Step 1(b): Row 2 copied from DRAM array to row buffer.** 

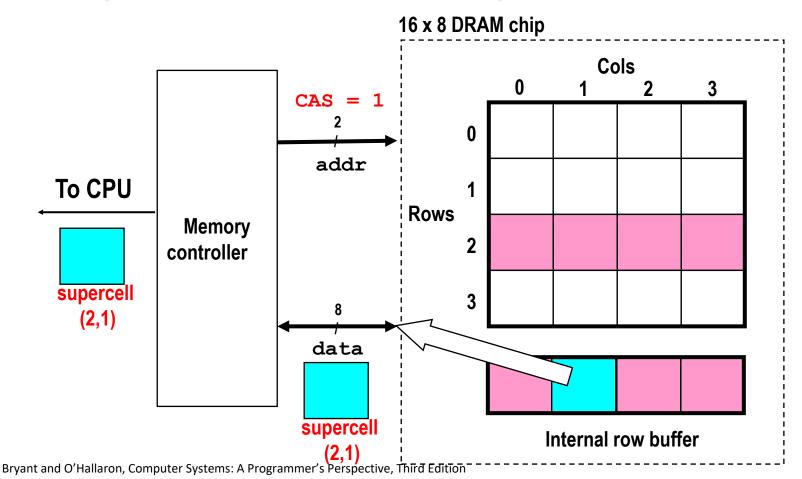


### Reading DRAM Supercell (2,1)

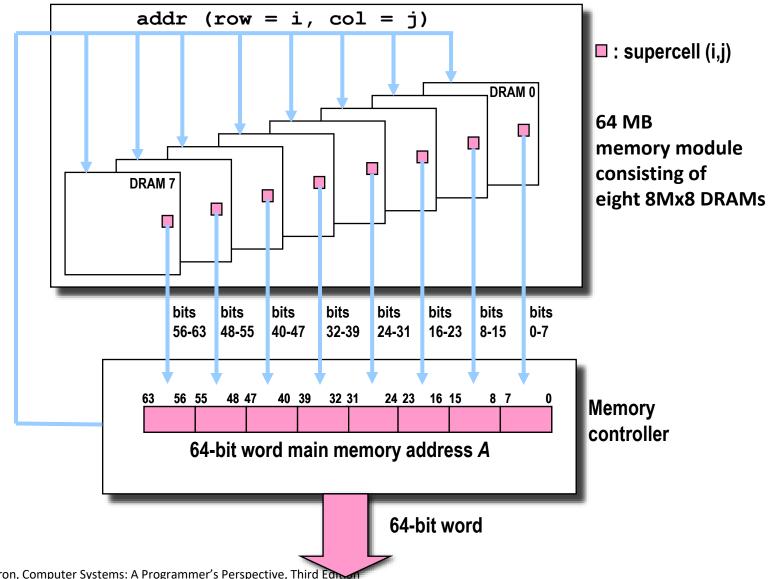
Step 2(a): Column access strobe (CAS) selects column 1.

Step 2(b): Supercell (2,1) copied from buffer to data lines, and eventually back to the CPU.

Step 3: All data written back to row to provide refresh



### **Memory Modules**

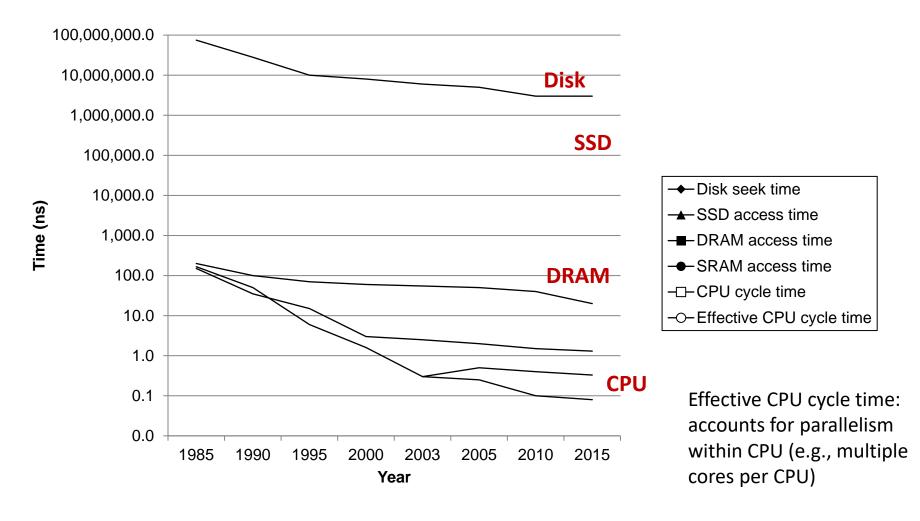


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### The CPU-Memory Gap

The gap widens between DRAM, disk, and CPU speeds.



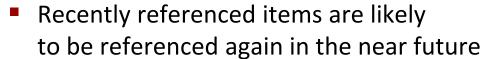
### Locality to the Rescue!

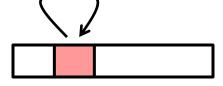
The key to bridging this CPU-Memory gap is a fundamental property of computer programs known as locality.

### Locality

 Principle of Locality: Programs tend to use data and instructions with addresses near or equal to those they have used recently

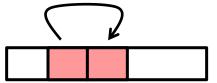








 Items with nearby addresses tend to be referenced close together in time



### **Locality Example**

```
sum = 0;
for (i = 0; i < n; i++)
    sum += a[i];
return sum;</pre>
```

#### Data references

 Reference array elements in succession (stride-1 reference pattern).

Reference variable sum each iteration.

#### Instruction references

Reference instructions in sequence.

Cycle through loop repeatedly.

## Spatial or Temporal Locality?

spatial

temporal

spatial

temporal

### **Qualitative Estimates of Locality**

Claim: Being able to look at code and get a qualitative sense of its locality is a key skill for a professional programmer.

Question: Does this function have good locality with

respect to array a?

Hint: array layout is row-major order

Answer: yes
Stride-1 reference
pattern

```
int sum_array_rows(int a[M][N])
{
   int i, j, sum = 0;

   for (i = 0; i < M; i++)
        for (j = 0; j < N; j++)
            sum += a[i][j];
   return sum;
}</pre>
```

a		а	а		a	a	a
_		- a	_			_	[
[0]	• • •	[0]	[1]	• • •	[1]	[M-1]	[M-1]
[0]		[N-1]	[0]		[N-1]	[0]	[N-1]

### **Locality Example**

Question: Does this function have good locality with respect to array a?

```
int sum_array_cols(int a[M][N])
{
   int i, j, sum = 0;

   for (j = 0; j < N; j++)
        for (i = 0; i < M; i++)
        sum += a[i][j];
   return sum;
}</pre>
```

**Answer: no** 

Stride N reference pattern

Note: If M is very small then good locality. Why?

a [0] [0]		a [0] [N-1]	a [1] [0]	• • •	a [1] [N-1]	•	•	٠	a [M-1] [0]		a [M-1] [N-1]
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### **Locality Example**

Question: Can you permute the loops so that the function scans the 3-d array a with a stride-1 reference pattern (and thus has good spatial locality)?

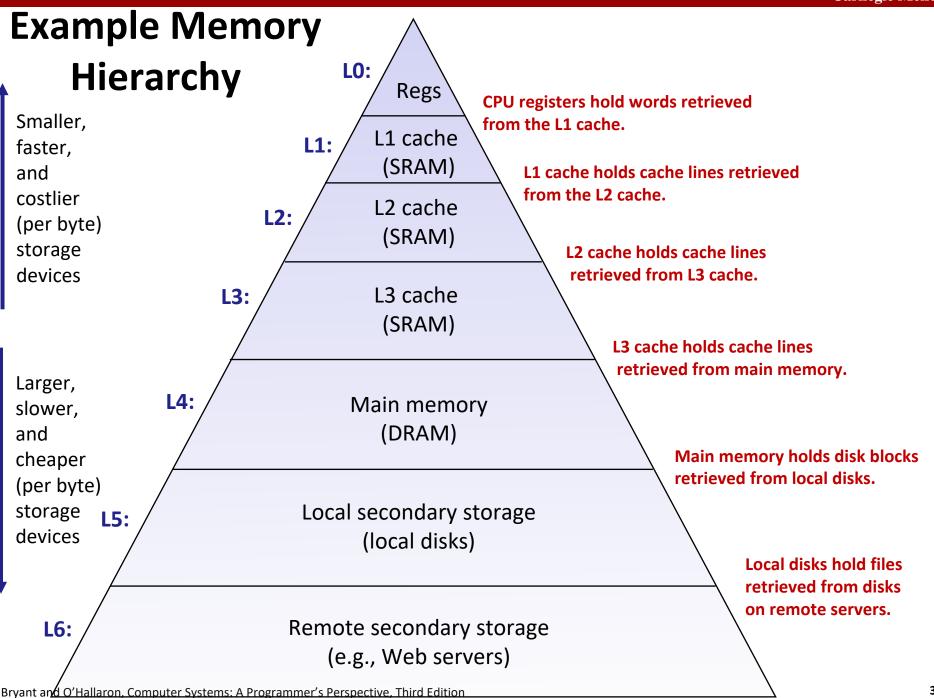
**Answer: make j the inner loop** 

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### **Memory Hierarchies**

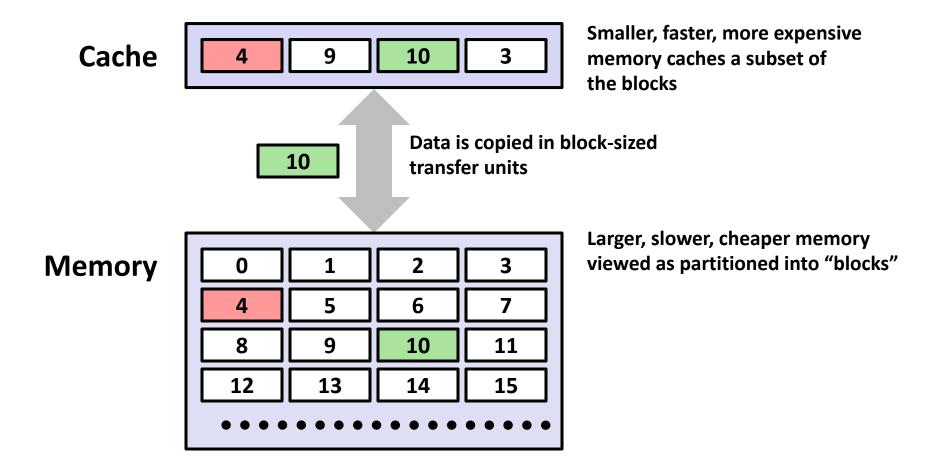
- Some fundamental and enduring properties of hardware and software:
  - Fast storage technologies cost more per byte, have less capacity, and require more power (heat!).
  - The gap between CPU and main memory speed is widening.
  - Well-written programs tend to exhibit good locality.
- These fundamental properties complement each other beautifully.
- They suggest an approach for organizing memory and storage systems known as a memory hierarchy.



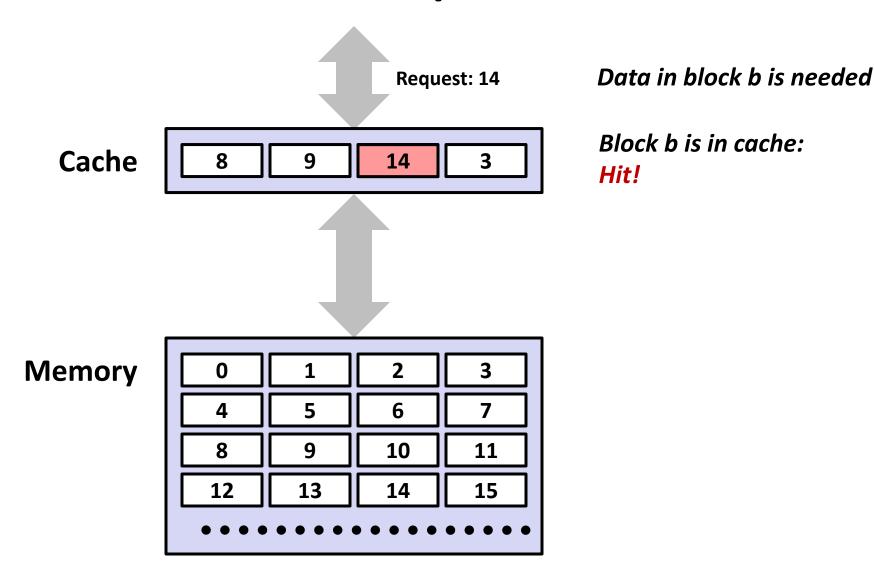
#### **Caches**

- Cache: A smaller, faster storage device that acts as a staging area for a subset of the data in a larger, slower device.
- Fundamental idea of a memory hierarchy:
  - For each k, the faster, smaller device at level k serves as a cache for the larger, slower device at level k+1.
- Why do memory hierarchies work?
  - Because of locality, programs tend to access the data at level k more often than they access the data at level k+1.
  - Thus, the storage at level k+1 can be slower, and thus larger and cheaper per bit.
- Big Idea (Ideal): The memory hierarchy creates a large pool of storage that costs as much as the cheap storage near the bottom, but that serves data to programs at the rate of the fast storage near the top.

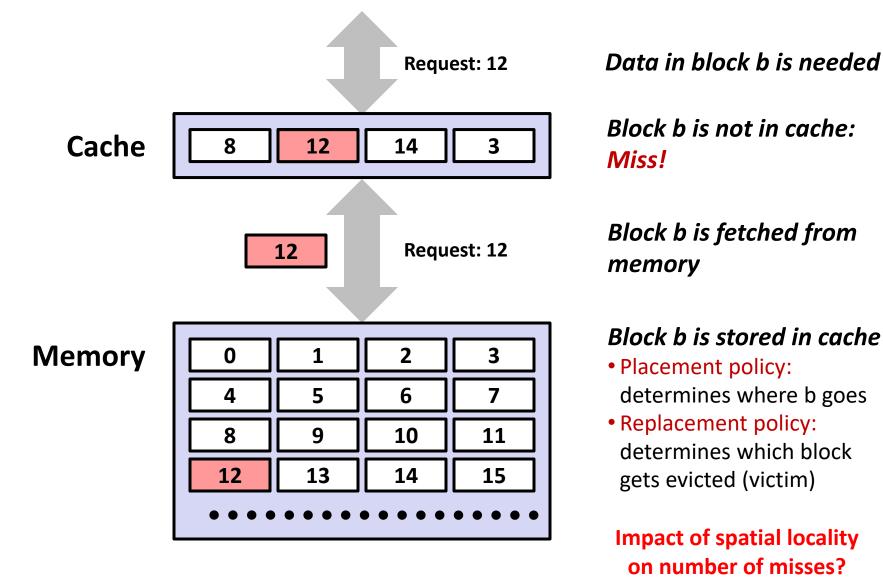
### **General Cache Concepts**



### **General Cache Concepts: Hit**



### **General Cache Concepts: Miss**



# **General Caching Concepts: 3 Types of Cache Misses**

#### ■ Cold (compulsory) miss

 Cold misses occur because the cache starts empty and this is the first reference to the block.

#### Capacity miss

 Occurs when the set of active cache blocks (working set) is larger than the cache.

#### Conflict miss

- Most caches limit blocks at level k+1 to a small subset (sometimes a singleton) of the block positions at level k.
  - E.g. Block i at level k+1 must be placed in block (i mod 4) at level k.
- Conflict misses occur when the level k cache is large enough, but multiple data objects all map to the same level k block.
  - E.g. Referencing blocks 0, 8, 0, 8, ... would miss every time.

# **Examples of Caching in the Mem. Hierarchy**

Cache Type	What is Cached?	Where is it Cached?	Latency (cycles)	Managed By
Registers	4-8 byte words	CPU core	0	Compiler
TLB	Address translations	On-Chip TLB	0	Hardware MMU
L1 cache	64-byte blocks	On-Chip L1	4	Hardware
L2 cache	64-byte blocks	On-Chip L2	10	Hardware
Virtual Memory	4-KB pages	Main memory	100	Hardware + OS
Buffer cache	Parts of files	Main memory	100	os
Disk cache	Disk sectors	Disk controller	100,000	Disk firmware
Network buffer cache	Parts of files	Local disk	10,000,000	NFS client
Browser cache	Web pages	Local disk	10,000,000	Web browser
Web cache	Web pages	Remote server disks	1,000,000,000	Web proxy server

### **Quiz Time!**

Check out:

https://canvas.cmu.edu/courses/20895

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- Locality of reference
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- Storage technologies and trends

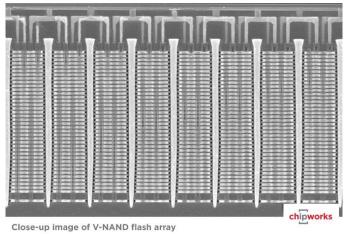
### **Storage Technologies**

Magnetic Disks



- Store on magnetic medium
- Electromechanical access

Nonvolatile (Flash)Memory



- Store as persistent charge
- Implemented with 3-D structure
  - 100+ levels of cells
  - 3 bits data per cell

#### What's Inside A Disk Drive?

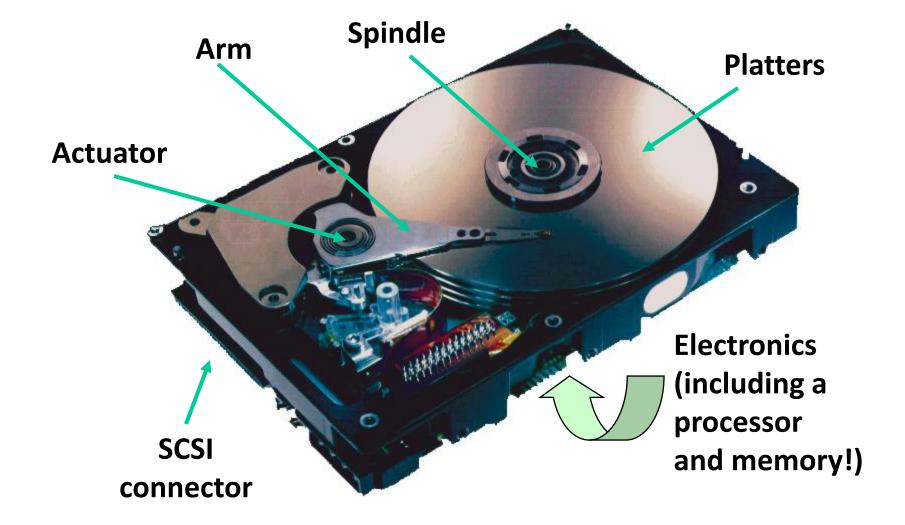
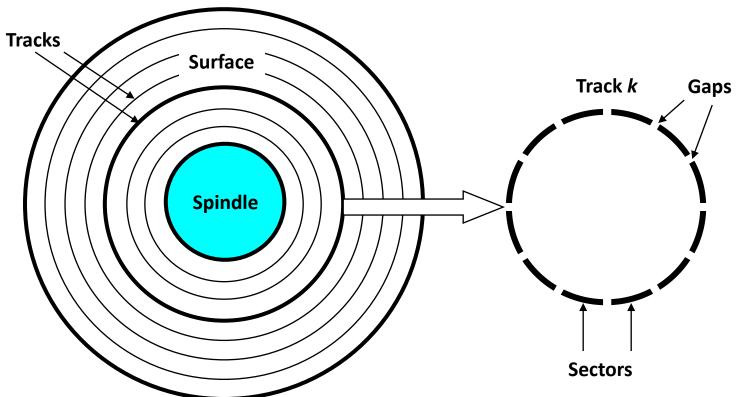


Image courtesy of Seagate Technology

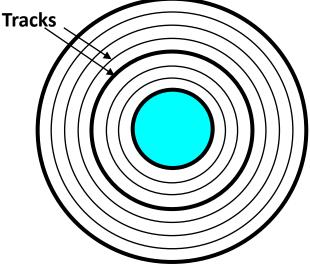
### **Disk Geometry**

- Disks consist of platters, each with two surfaces.
- Each surface consists of concentric rings called tracks.
- Each track consists of sectors separated by gaps.



### **Disk Capacity**

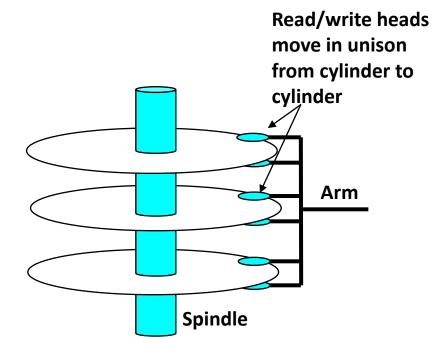
- Capacity: maximum number of bits that can be stored.
  - Vendors express capacity in units of gigabytes (GB) or terabytes (TB), where 1 GB =  $10^9$  Bytes and 1 TB =  $10^{12}$  Bytes
- Capacity is determined by these technology factors:
  - Recording density (bits/in): number of bits that can be squeezed into a 1 inch segment of a track.
  - Track density (tracks/in): number of tracks that can be squeezed into a 1 inch radial segment.
  - Areal density (bits/in²): product of recording and track density.



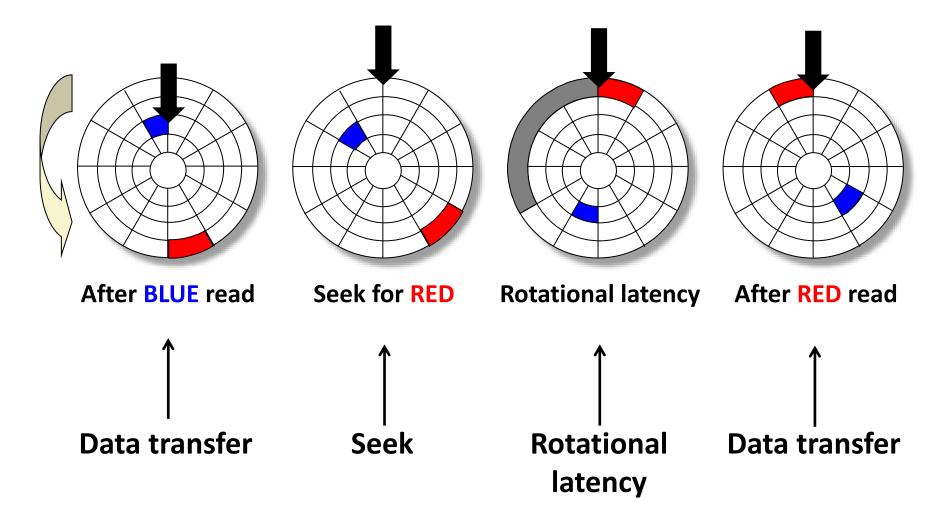
# **Disk Operation (Single-Platter View)**

The disk surface The read/write *head* spins at a fixed is attached to the end rotational rate of the arm and flies over the disk surface on a thin cushion of air. spindle By moving radially, the arm can position the read/write head over any track.

### **Disk Operation (Multi-Platter View)**



# **Disk Access – Service Time Components**



#### **Disk Access Time**

#### Average time to access some target sector approximated by:

- $T_{access} = T_{avg seek} + T_{avg rotation} + T_{avg transfer}$
- Seek time (T<sub>avg seek</sub>)
  - Time to position heads over cylinder containing target sector.
  - Typical T<sub>avg seek</sub> is 3—9 ms
- Rotational latency (T<sub>avg rotation</sub>)
  - Time waiting for first bit of target sector to pass under r/w head.
  - $T_{avg\ rotation} = 1/2 \times 1/RPMs \times 60 \sec/1 min$
  - Typical rotational rate = 7,200 RPMs
- Transfer time (T<sub>avg transfer</sub>)
  - Time to read the bits in the target sector.
  - $T_{avg transfer} = 1/RPM \times 1/(avg # sectors/track) \times 60 secs/1 min$

time for one rotation (in minutes) fraction of a rotation to be read

### **Disk Access Time Example**

#### Given:

- Rotational rate = 7,200 RPM
- Average seek time = 9 ms
- Avg # sectors/track = 400

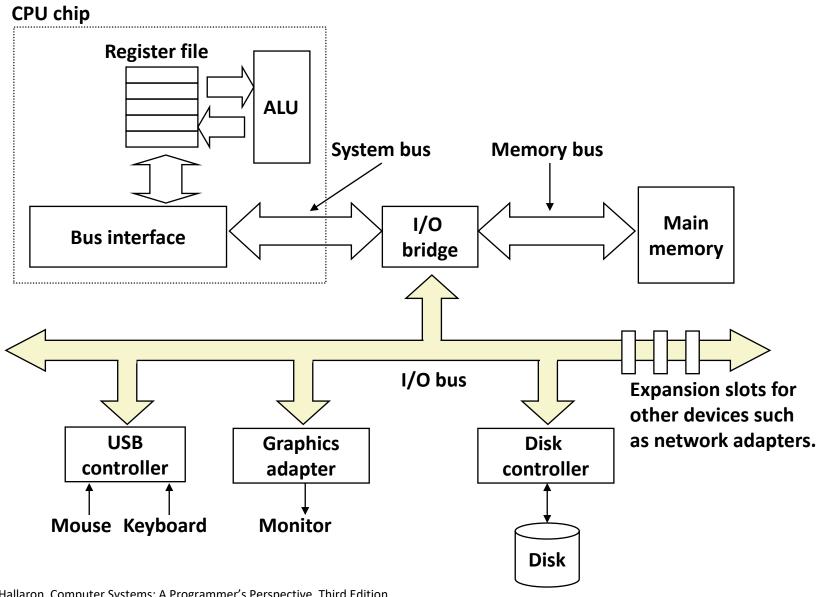
#### Derived:

- $T_{avg\ rotation} = 1/2\ x\ (60\ secs/7200\ RPM)\ x\ 1000\ ms/sec = 4\ ms$
- $T_{avg transfer} = 60/7200 \times 1/400 \times 1000 \text{ ms/sec} = 0.02 \text{ ms}$
- $T_{access} = 9 \text{ ms} + 4 \text{ ms} + 0.02 \text{ ms}$

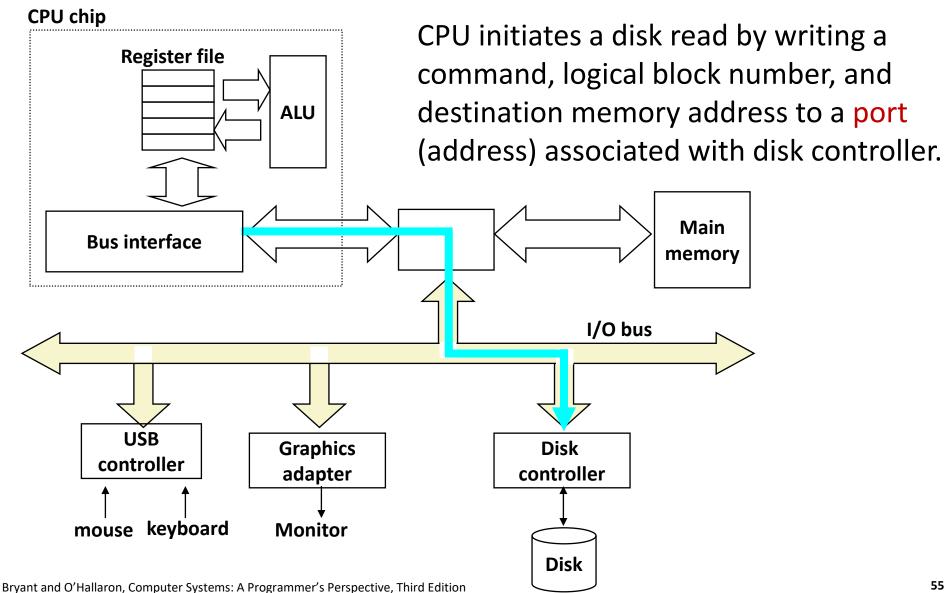
#### Important points:

- Access time dominated by seek time and rotational latency.
- First bit in a sector is the most expensive, the rest are free.
- SRAM access time is about 4 ns/doubleword, DRAM about 60 ns
  - Disk is about 40,000 times slower than SRAM,
  - 2,500 times slower than DRAM.

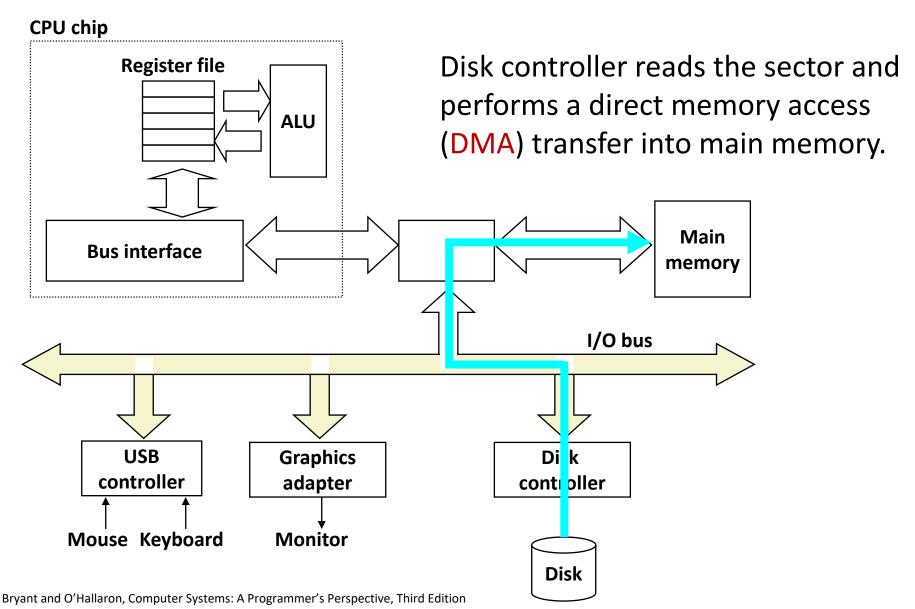
# I/O Bus



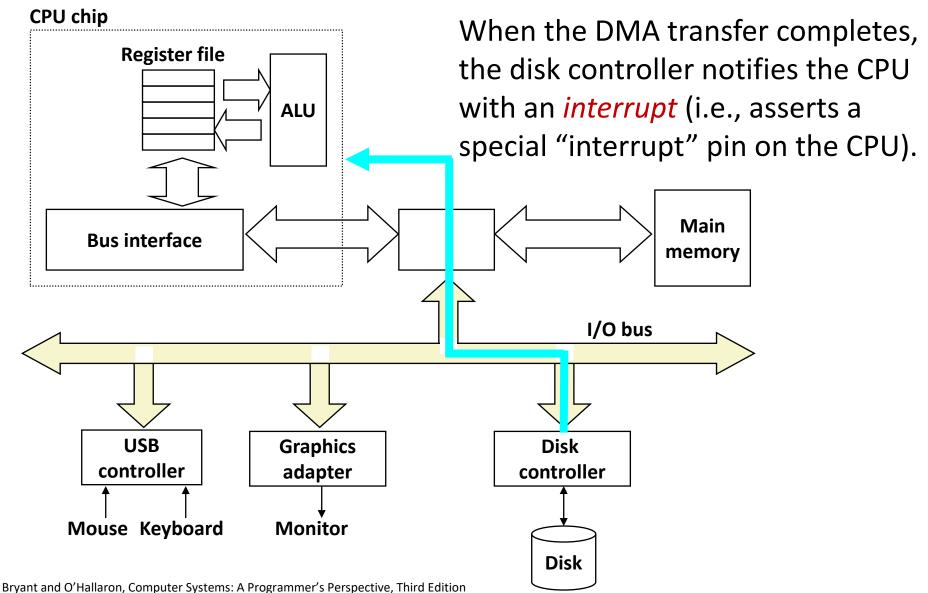
# Reading a Disk Sector (1)



# Reading a Disk Sector (2)



# Reading a Disk Sector (3)



#### **Nonvolatile Memories**

#### DRAM and SRAM are volatile memories

Lose information if powered off.

#### Nonvolatile memories retain value even if powered off

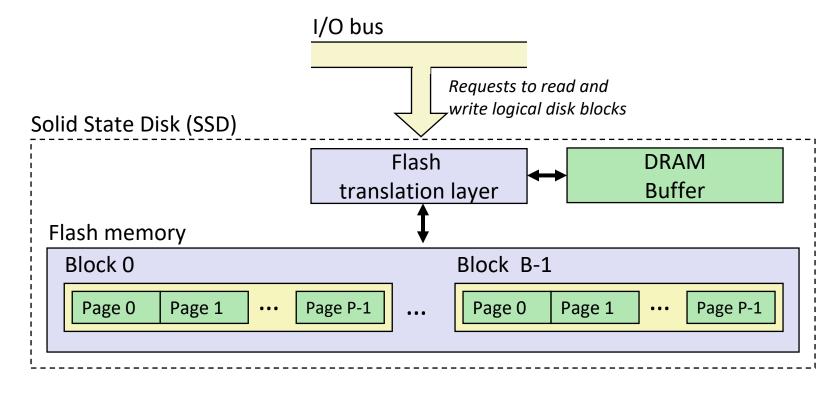
- Read-only memory (ROM): programmed during production
- Electrically eraseable PROM (EEPROM): electronic erase capability
- Flash memory: EEPROMs, with partial (block-level) erase capability
  - Wears out after about 100,000 erasings
- 3D XPoint (Intel Optane) & emerging NVMs
  - New materials



#### Uses for Nonvolatile Memories

- Firmware programs stored in a ROM (BIOS, controllers for disks, network cards, graphics accelerators, security subsystems,...)
- Solid state disks (replacing rotating disks)
- Disk caches

# Solid State Disks (SSDs)



- Pages: 512KB to 4KB, Blocks: 32 to 128 pages
- Data read/written in units of pages.
- Page can be written only after its block has been erased.
- A block wears out after about 100,000 repeated writes.

#### **SSD Performance Characteristics**

Benchmark of Samsung 940 EVO Plus

https://ssd.userbenchmark.com/SpeedTest/711305/Samsung-SSD-970-EVO-Plus-250GB

Sequential read throughput 2,126 MB/s Sequential write tput 1,880 MB/s Random read throughput 140 MB/s Random write tput 59 MB/s

- Sequential access faster than random access
  - Common theme in the memory hierarchy
- Random writes are somewhat slower
  - Erasing a block takes a long time (~1 ms).
  - Modifying a block page requires all other pages to be copied to new block.
  - Flash translation layer allows accumulating series of small writes before doing block write.

### **SSD Tradeoffs vs Rotating Disks**

#### Advantages

■ No moving parts → faster, less power, more rugged

#### Disadvantages

- Have the potential to wear out
  - Mitigated by "wear leveling logic" in flash translation layer
  - E.g. Samsung 940 EVO Plus guarantees 600 writes/byte of writes before they wear out
  - Controller migrates data to minimize wear level
- In 2019, about 4 times more expensive per byte
  - And, relative cost will keep dropping

#### Applications

- Smartphones, laptops
- Increasingly common in desktops and servers

### **Summary**

- The speed gap between CPU, memory and mass storage continues to widen.
- Well-written programs exhibit a property called *locality*.
- Memory hierarchies based on caching close the gap by exploiting locality.
- Flash memory progress outpacing all other memory and storage technologies (DRAM, SRAM, magnetic disk)
  - Able to stack cells in three dimensions

# **Supplemental slides**

### **Storage Trends**

#### **SRAM**

Metric	1985	1990	1995	2000	2005	2010	2015	2015:1985
\$/MB	2,900	320	256	100	<b>75</b>	60	320	116
access (ns)	150	<b>35</b>	15	3	2	1.5	200	115

#### **DRAM**

Metric	1985	1990	1995	2000	2005	2010	2015	2015:1985
\$/MB	880	100	30	1	0.1	0.06	0.02	44,000
access (ns)	200	100	<b>70</b>	60	<b>50</b>	40	20	10
typical size (MB)	0.256	4	16	64	2,000	8,000	16.000	62,500

#### **Disk**

Metric	1985	1990	1995	2000	2005	2010	2015	2015:1985
\$/GB access (ms)	100,000 75	8,000 28	300 10	10 8	5 5	0.3	0.03 3	3,333,333 25
typical size (GB)	0.01	0.16	1	20	160	1,500	3,000	300,000

Bryant and O'Hallaron, Computer Systems: A Programmer's Perspective, Third Edition

#### **CPU Clock Rates**

Inflection point in computer history when designers hit the "Power Wall"

	1985	1990	1995	2003	2005	2010	2015	2015:1985
СРИ	80286	80386	Pentium	P-4	Core 2	Core i7(n	) Core i7(h	)
Clock rate (MHz	) 6	20	150	3,300	2,000	2,500	3,000	500
Cycle time (ns)	166	50	6	0.30	0.50	0.4	0.33	500
Cores	1	1	1	1	2	4	4	4
Effective cycle time (ns)	166	50	6	0.30	0.25	0.10	0.08	2,075